Table I: Chemical composition of the 300-cycle InN samples as a function of varying plasma chemistry in terms of atomic concentration (measured from the surface of the films).

$Ar/N_2/H_2$ (sccm)	In at. %	N at. %	O at. %	C at. %
50/50/0	28.2	29.7	17.9	24.2
0/50/0	24.4	27.6	18.7	29.3
50/50/50	26.4	5.0	44.0	24.0

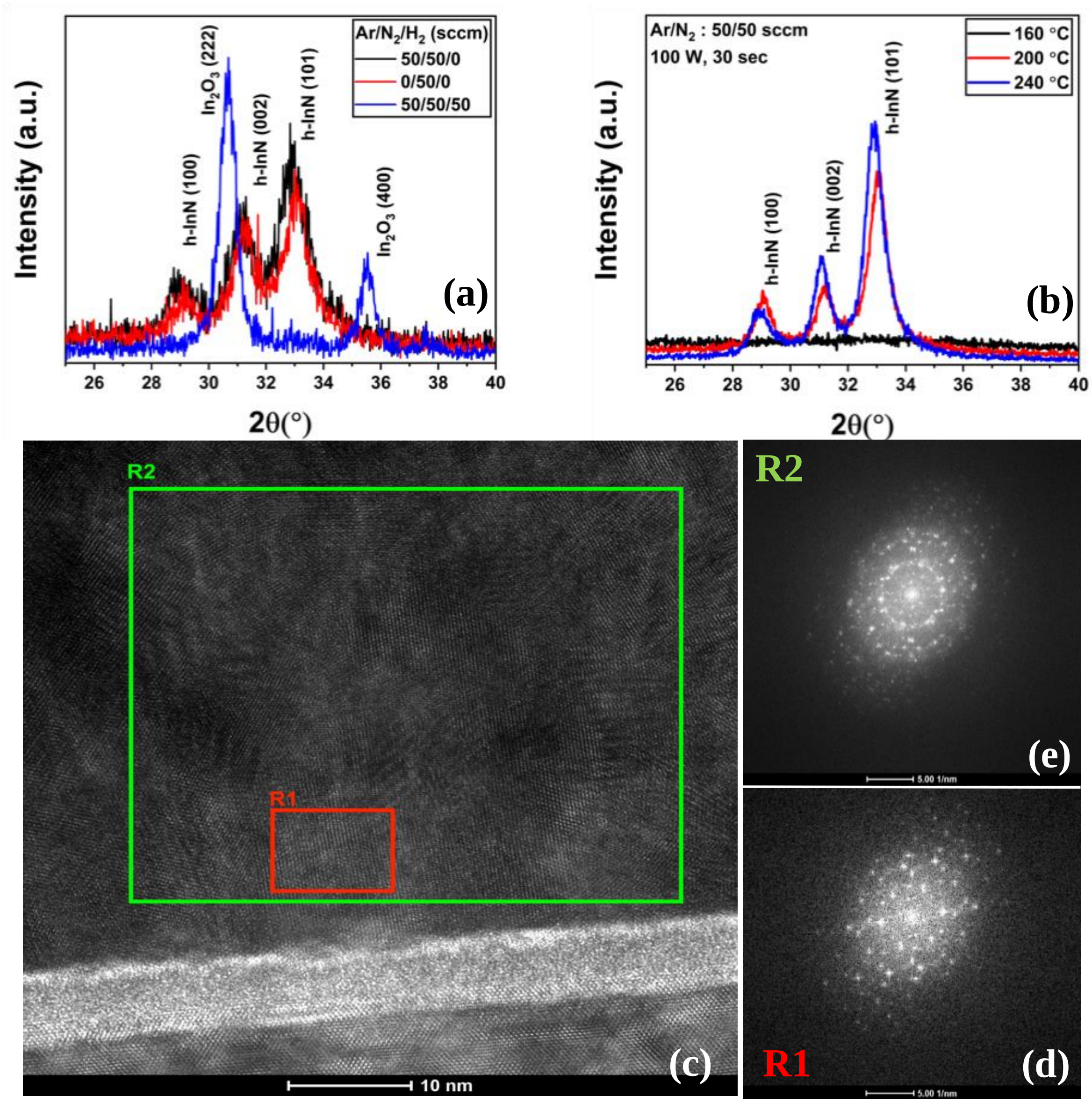

Figure 1. GIXRD measurement spectra of the sample deposited (a) with 100 W plasma power, 200 °C, and varying plasma chemistry. (b) at variable substrate temperatures. (c) HR-TEM image of InN film deposited at 240 °C with 100 W rf-power. Fast Fourier transform (FFT) of the film crystal structure under the selected-region R2. (e) under the selected-region R1.